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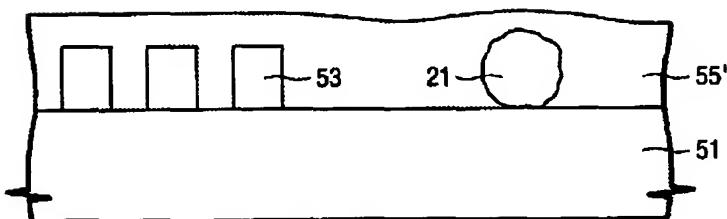
(54) Title of Invention

METHOD FOR FABRICATING SPIN-ON-GLASS INSULATION LAYER OF SEMICONDUCTOR DEVICE

Representative drawing

(57) Abstract:

PURPOSE: A method for fabricating a spin-on-glass(SOG) insulation layer of a semiconductor device is provided to control particles caused by gas generated from the SOG layer and to prevent a crack on the SOG layer after a high temperature annealing process, by using the SOG layer in a portion where patterns are dense.



CONSTITUTION: The SOG insulation layer(55) is applied on a substrate(51) having a plurality of stepped patterns by using poly silazane of a solution state. A pre-bake process is performed within a temperature range of 50-350 deg.C to eliminate a solvent component of the insulation layer. A hard bake process is performed within a temperature range of 350-500 deg.C. An annealing process is performed within a temperature scope of

600-1200 deg.C.

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